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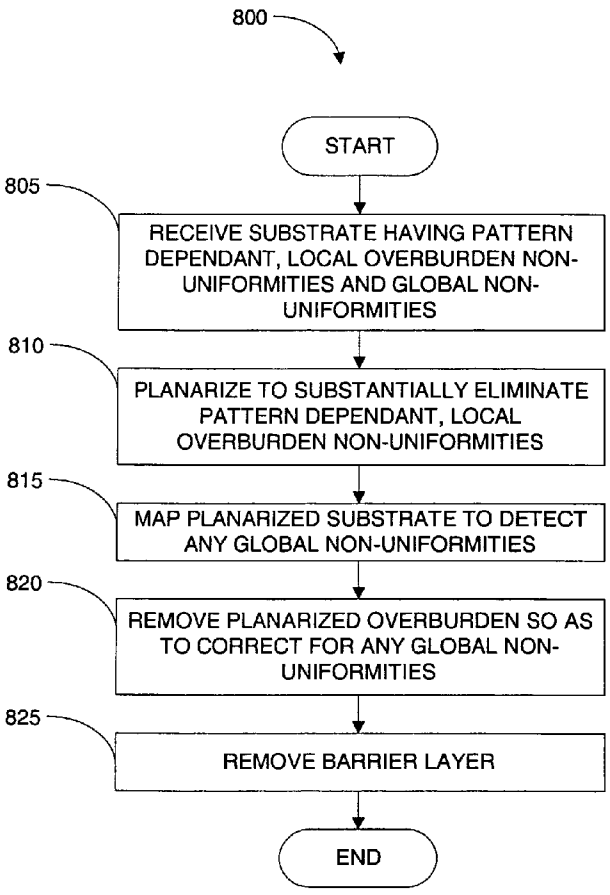
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(54) Title: SYSTEM, METHOD AND APPARATUS FOR IMPROVED GLOBAL DUAL-DAMASCENE PLANARIZATION



(57) Abstract: A system and method for planarizing a patterned semiconductor substrate (100) includes receiving a patterned semiconductor substrate. The patterned semiconductor substrate (100) having a conductive interconnect material (120) filling multiple of features in the pattern. The conductive interconnect material has an overburden portion (112). The overburden portion has a localized non-uniformity. A bulk portion of the overburden portion is removed to planarize the overburden portion (120). The substantially locally planarized overburden portion is mapped to determine a global non-uniformity. The substantially locally planarized overburden portion is etched to substantially remove the global non-uniformity.

WO 2004/084266 A3

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